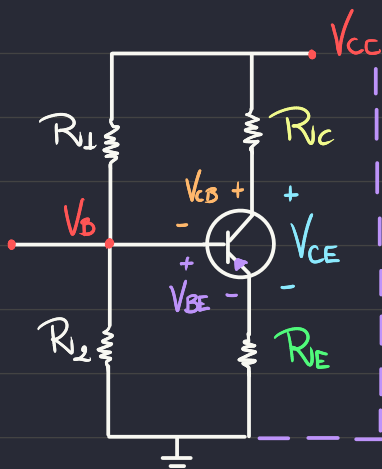


Lista 5 \Rightarrow

1)



$$V_{CC} = -15V \quad R_C = 1,2 k\Omega$$

$$R_E = 330\Omega \quad R_{L1} = 10 k\Omega$$

$$R_{L2} = 3,3 k\Omega \quad \beta = 100$$

- Determine V_B , V_E , V_C e I_C (em mA):

$$V_{CC} = -15V$$



$$\Rightarrow V_B = V_{CC} \cdot \frac{R_{L2}}{R_{L1} + R_{L2}} \rightarrow$$

$$V_B = -15 \cdot \frac{3,3 \cdot 10^3}{10 \cdot 10^3 + 3,3 \cdot 10^3} = -3,702V$$

\rightarrow Como $I_E \cong I_C$, então: Transistor de Si

$$I_C \cong I_E \cong \frac{V_B - V_{BE}}{R_E} = \frac{-3,702 - (-0,7)}{330} \Rightarrow$$

$$I_C = -9,158 mA$$

→ Utilizando a análise aproximada, temos que:

$$V_{CE} = V_{CC} - I_C (R_{IC} + R_{IE}) \rightarrow$$

$$V_{CE} = -15 - (-9,158\text{mA})(1,2\text{k} + 330) \rightarrow$$

$$V_{CE} = -15 + 14,0117 = 0,988\text{V}$$

→ Por fim, encontrando V_C :

$$V_C = V_{CE} + V_E = -0,988 - 3,722 - (-0,7\text{V})$$

$$V_C = -4,01\text{V}$$

$$V_E = -3,722 - (0,7) = -4,422$$

2)



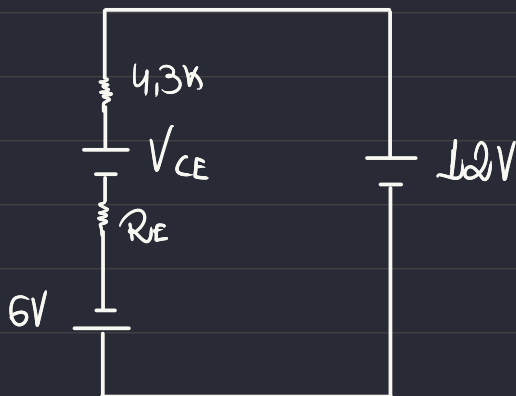
$$R_c = 4,3k\Omega \quad V_{BE} = 0,7V$$

$$\beta = 50 \quad V_{CE} = 4V$$

• Considerando $I_E = I_B + I_C$.

$$V_{RE} = 6 - V_{BE} = 5,3V$$

a)



$$-6 - 12 + 4,3kI_C + V_{CE} + 5,3 = 0 \rightarrow$$

$$4,3kI_C = 6 + 12 - 4 - 5,3 \rightarrow$$

$$4,3kI_C = 8,7 \rightarrow$$

$$I_C = \frac{8,7}{4,3k} = 2,023mA$$

→ Utilizando o ganho para encontrar o I_B :

$$I_C = \beta \cdot I_B \rightarrow I_B = \frac{2,023mA}{50} = 40,46\mu A$$

$$I_E = I_B + I_C = 40,46 \cdot 10^{-6} + 2,023 \cdot 10^{-3}$$

$$I_E = 2,063mA$$

$$R_{RE} = \frac{V_{RE}}{I_E} = \frac{5,3}{2,063mA} \rightarrow R_{RE} = 2,569k\Omega$$

b) Considerando que $\frac{\partial I_B}{\partial I_C} = 0$:

$$S = \frac{1 + \beta}{1 - \beta \frac{\partial I_B}{\partial I_C}} = 1 + \beta = 1 + 50 \rightarrow$$

$$S = 51$$